

ABSTRACT OF THE DISCLOSURE

The invention includes capacitor constructions comprising a layer of aluminum oxide between a high-k dielectric material and a layer comprising titanium and nitrogen. The layer comprising titanium and nitrogen can be, for example, titanium nitride and/or boron-doped titanium nitride. The capacitor constructions can be incorporated into DRAM cells, which in turn can be incorporated into electronic systems. The invention also includes methods of forming capacitor constructions.